

**Amendment and Response**

Applicant: Thomas C. Anthony et al.

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Title: MAGNETIC MEMORY DEVICE

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**IN THE SPECIFICATION**

Please amend paragraph 27 of the specification to read as follows:

Data is stored as an orientation of magnetization in the magnetic layers of bit cell 130. As illustrated in Figure 4, bit cell 130 includes an active magnetic data film 132 (sense layer) and a pinned magnetic film 134 (reference layer), which are separated by a dielectric region 136 (tunnel barrier). The orientation of magnetization in sense layer 132 is not fixed and can assume either of two stable orientations as shown by arrow  $M_1$  (i.e., sense layer 132 has free magnetic poles). In contrast, pinned reference layer 134 has a fixed orientation of magnetization, as shown by arrow  $M_2$ . Sense layer 132 rotates its orientation of magnetization in response to electrical currents applied to write lines 122 and 124 during a write operation directed to selected bit cells 130.